

Vladimir Aleshkin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

178
papers

1,086
citations

16
h-index

27
g-index

195
ext. papers

1,315
ext. citations

1.2
avg, IF

4.01
L-index

#	Paper	IF	Citations
178	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at ~6 μ m wavelength from HgCdTe quantum wells. <i>Journal of Applied Physics</i> , 2021 , 130, 214302	2.5	1
177	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. <i>Laser Physics</i> , 2021 , 31, 015801	1.2	2
176	Anomalous electron polarizability of HgTe quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021 , 128, 114606	3	0
175	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. <i>Journal of Applied Physics</i> , 2021 , 129, 133106	2.5	4
174	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. <i>Technical Physics Letters</i> , 2021 , 47, 154-157	0.7	1
173	Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. <i>Applied Optics</i> , 2021 , 60, 8991-8998	1.7	0
172	Model of a Terahertz Quantum-Cascade Laser Based on Two-Dimensional Plasmons. <i>Semiconductors</i> , 2021 , 55, 828-830	0.7	
171	Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2020 , 41, 750-757	2.2	2
170	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2020 , 127, 165701	2.5	0
169	HgCdTe-based quantum cascade lasers operating in the GaAs phonon Reststrahlen band predicted by the balance equation method. <i>Optics Express</i> , 2020 , 28, 25371-25382	3.3	9
168	Investigation of Stimulated Emission from HgTe/CdHgTe Quantum-Well Heterostructures in the 3 μ m Atmospheric Transparency Window. <i>Semiconductors</i> , 2020 , 54, 1365-1370	0.7	
167	Effects of the Electron-Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. <i>JETP Letters</i> , 2020 , 112, 508-512	1.2	0
166	Plasmon recombination in narrowgap HgTe quantum wells. <i>Journal of Physics Communications</i> , 2020 , 4, 115012	1.2	3
165	Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. <i>ACS Photonics</i> , 2020 , 7, 98-104	6.3	13
164	Anisotropy of the in-plane g-factor of electrons in HgTe quantum wells. <i>Physical Review B</i> , 2020 , 101,	3.3	1
163	Temperature limitations for stimulated emission in 3 μ m range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. <i>Applied Physics Letters</i> , 2020 , 117, 083103	3.4	8
162	Continuous-Wave Stimulated Emission in the 10 μ m-4 μ m Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. <i>Semiconductors</i> , 2020 , 54, 1371-1375	0.7	1

161	Investigation into Microwave Absorption in Semiconductors for Frequency-Multiplication Devices and Radiation-Output Control of Continuous and Pulsed Gyrotrons. <i>Semiconductors</i> , 2020 , 54, 1069-1074	0.7	2
160	Photoluminescence Spectra of InAs/GaInSb/InAs Quantum Wells in the Mid-Infrared Region. <i>Semiconductors</i> , 2020 , 54, 1119-1122	0.7	
159	Submonolayer InGaAs/GaAs Quantum Dots Grown by MOCVD. <i>Semiconductors</i> , 2019 , 53, 1138-1142	0.7	3
158	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd _{0.7} Hg _{0.3} Te QWs Near 14 μ m. <i>Semiconductors</i> , 2019 , 53, 1154-1157	0.7	4
157	Negative terahertz conductivity and amplification of surface plasmons in graphene/black phosphorus injection laser heterostructures. <i>Physical Review B</i> , 2019 , 100,	3.3	12
156	Effect of Cd content in barriers on the threshold energy of Auger recombination in waveguide structures with HgTe/Cd _x Hg _{1-x} Te quantum wells, emitting at a wavelength of 18 μ m. <i>Quantum Electronics</i> , 2019 , 49, 556-558	1.8	2
155	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. <i>JETP Letters</i> , 2019 , 109, 191-197	1.2	1
154	Carrier Recombination, Long-Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800546	1.3	10
153	Spin-orbit splitting of the conduction band in HgTe quantum wells: Role of different mechanisms. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2019 , 110, 95-99	3	2
152	Threshold energies of Auger recombination in HgTe/CdHgTe quantum well heterostructures with 30-70 meV bandgap. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 425301	1.8	4
151	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 145501	1.8	10
150	Interband infrared photodetectors based on HgTe/CdHgTe quantum-well heterostructures. <i>Optical Materials Express</i> , 2018 , 8, 1349	2.6	10
149	Magneto-optical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. <i>Semiconductors</i> , 2018 , 52, 436-441	0.7	
148	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. <i>Crystals</i> , 2018 , 8, 311	2.3	9
147	Lowering the Lasing Threshold by Doping in Mid-Infrared Lasers Based on HgCdTe with HgTe Quantum Wells. <i>Semiconductors</i> , 2018 , 52, 1221-1224	0.7	3
146	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , 2018 , 52, 1547-1550	0.7	3
145	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. <i>JETP Letters</i> , 2018 , 108, 329-334	1.2	2
144	HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. <i>Journal of Physics: Conference Series</i> , 2018 , 1092, 012126	0.3	

143	Photodetectors with an InGaAs Active Region and InGaP Metamorphic Buffer Layer Grown on GaAs Substrates. <i>Semiconductors</i> , 2018 , 52, 1564-1567	0.7	
142	Magneto-optics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. <i>Semiconductors</i> , 2018 , 52, 1386-1391	0.7	0
141	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. <i>Journal of Physics Condensed Matter</i> , 2018 , 30, 495301	1.8	10
140	Stimulated Emission in the 1.3–1.5 μm Spectral Range from AlGaInAs Quantum Wells in Hybrid Light-Emitting III–V Heterostructures on Silicon Substrates. <i>Semiconductors</i> , 2018 , 52, 1495-1499	0.7	
139	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. <i>Semiconductors</i> , 2018 , 52, 1375-1379	0.7	4
138	Stimulated Emission at 1.3- μm Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , 2018 , 44, 735-738	0.7	
137	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , 2017 , 51, 663-666	0.7	5
136	Valence band energy spectrum of HgTe quantum wells with an inverted band structure. <i>Physical Review B</i> , 2017 , 96,	3.3	22
135	Activation conductivity in HgTe/CdHgTe quantum wells at integer Landau level filling factors: Role of the random potential. <i>Semiconductors</i> , 2017 , 51, 1562-1570	0.7	
134	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. <i>Semiconductors</i> , 2017 , 51, 1531-1536	0.7	5
133	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , 2017 , 51, 1477-1480	0.7	4
132	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. <i>Semiconductors</i> , 2017 , 51, 1527-1530	0.7	5
131	On the cascade capture of electrons at charged dipoles in weakly compensated semiconductors. <i>Semiconductors</i> , 2017 , 51, 1444-1448	0.7	1
130	Dual-frequency GaAs/InGaP laser diode with a GaAsSb quantum well. <i>Semiconductors</i> , 2017 , 51, 1360-1363	0.7	1
129	Variation of the emission frequency of a terahertz quantum cascade laser. <i>Technical Physics Letters</i> , 2016 , 42, 230-233	0.7	
128	Magneto-spectroscopy of double HgTe/CdHgTe quantum wells. <i>Semiconductors</i> , 2016 , 50, 1532-1538	0.7	8
127	The exciton excitations and relaxation processes in low-dimensional semiconductor heterostructures with quantum wells. <i>Semiconductors</i> , 2016 , 50, 1691-1695	0.7	
126	Dynamics of the cascade capture of electrons by charged donors in GaAs and InP. <i>Journal of Experimental and Theoretical Physics</i> , 2016 , 123, 284-291	1	3

125	Method for narrowing the directional pattern of an InGaAs/GaAs/AlGaAs multiwell heterolaser. <i>Semiconductors</i> , 2016 , 50, 1488-1492	0.7	
124	Stimulated emission from a metamorphic GaAsSb bulk layer on a GaAs substrate. <i>Semiconductors</i> , 2016 , 50, 586-589	0.7	
123	Stimulated emission in heterostructures with double InGaAs/GaAsSb/GaAs quantum wells, grown on GaAs and Ge/Si(001) substrates. <i>Semiconductors</i> , 2016 , 50, 1435-1438	0.7	3
122	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. <i>Applied Physics Letters</i> , 2016 , 109, 061111	3.4	19
121	Observation of dynamics of impurity photoconductivity in n-GaAs caused by electron cooling. <i>Semiconductors</i> , 2015 , 49, 113-117	0.7	3
120	Graphene vertical cascade interband terahertz and infrared photodetectors. <i>2D Materials</i> , 2015 , 2, 025002	0.7	19
119	An observation of direct-gap electroluminescence in GaAs structures with Ge quantum wells. <i>Semiconductors</i> , 2015 , 49, 170-173	0.7	
118	Optical characteristics of laser diodes based on A3B5 compounds grown on germanium substrates. <i>Technical Physics Letters</i> , 2015 , 41, 304-306	0.7	
117	Nonlinear harmonic mixing in an InGaAs/InGaP/GaAs laser on a germanium substrate. <i>Quantum Electronics</i> , 2015 , 45, 204-206	1.8	1
116	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , 2015 , 41, 648-650	0.7	2
115	The temporal dynamics of impurity photoconductivity in quantum wells in GaAs. <i>Journal of Experimental and Theoretical Physics</i> , 2015 , 121, 647-652	1	1
114	On the cascade capture of electrons at donors in GaAs quantum wells. <i>Semiconductors</i> , 2015 , 49, 1197-1201	0.7	
113	On a semiconductor laser with a p \bar{n} tunnel junction with radiation emission through the substrate. <i>Semiconductors</i> , 2015 , 49, 1440-1442	0.7	1
112	Optimization of InGaP/GaAs/InGaAs heterolasers with tunnel-coupled waveguides. <i>Semiconductors</i> , 2015 , 49, 1571-1574	0.7	1
111	Stimulated emission from an InGaAs/GaAs/AlGaAs heterostructure grown on a Si substrate. <i>JETP Letters</i> , 2015 , 100, 795-797	1.2	4
110	Efficiency of vertical emission from a semiconductor laser waveguide with a diffraction grating. <i>Semiconductors</i> , 2014 , 48, 89-94	0.7	3
109	1.3 μ m photoluminescence of Ge/GaAs multi-quantum-well structure. <i>Journal of Applied Physics</i> , 2014 , 115, 043512	2.5	6
108	Voltage-tunable terahertz and infrared photodetectors based on double-graphene-layer structures. <i>Applied Physics Letters</i> , 2014 , 104, 163505	3.4	25

107	Surface-plasmons lasing in double-graphene-layer structures. <i>Journal of Applied Physics</i> , 2014 , 115, 044513	1.5	14
106	Near-field effect in the absorption spectrum of impurities in crystals. <i>JETP Letters</i> , 2014 , 99, 712-714	1.2	
105	Investigation of GaAs/AlGaAs quantum cascade structures by optical methods based on hot luminescence in the near-infrared range. <i>Semiconductors</i> , 2014 , 48, 1463-1466	0.7	
104	Temporal dynamics of impurity photoconductivity in n-GaAs and n-InP. <i>Physics of the Solid State</i> , 2014 , 56, 917-921	0.8	1
103	Experimental determination of the optimum number of quantum wells in multiwell heterolasers with radiation leakage into a substrate. <i>Technical Physics Letters</i> , 2014 , 40, 432-434	0.7	2
102	Substrate-emitting semiconductor laser with a trapezoidal active region. <i>Quantum Electronics</i> , 2014 , 44, 286-288	1.8	1
101	Dependence of the ground-state transition energy versus optical pumping in GaAsSb/InGaAs/GaAs heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 021108	3.4	3
100	Long-wavelength shift and enhanced room temperature photoluminescence efficiency in GaAsSb/InGaAs/GaAs-based heterostructures emitting in the spectral range of 1.0-1.2 μm due to increased charge carrier localization. <i>Journal of Applied Physics</i> , 2014 , 116, 203102	2.5	1
99	Guiding effect of quantum wells in semiconductor lasers. <i>Quantum Electronics</i> , 2013 , 43, 401-406	1.8	5
98	Injection terahertz laser using the resonant inter-layer radiative transitions in double-graphene-layer structure. <i>Applied Physics Letters</i> , 2013 , 103, 163507	3.4	34
97	Nonresonant radiative exciton transfer by near field between quantum wells. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 117, 944-949	1	1
96	Waveguide effect of GaAsSb quantum wells in a laser structure based on GaAs. <i>Semiconductors</i> , 2013 , 47, 1475-1477	0.7	6
95	Spectral-kinetic properties of heterostructures with GaAsSb/InGaAs/GaAs-based quantum wells emitting in the range of 1.0-1.2 μm . <i>Semiconductors</i> , 2013 , 47, 1504-1507	0.7	
94	Resonance Coulomb scattering at shallow donors in AlGaAs/n-GaAs/AlGaAs quantum wells. <i>Semiconductors</i> , 2013 , 47, 487-493	0.7	
93	Structural and optical properties of GaAs-based heterostructures with Ge and Ge/InGaAs quantum wells. <i>Semiconductors</i> , 2013 , 47, 636-640	0.7	3
92	Shot noise suppression and coherent tunneling in a triple barrier resonant diode 2013 ,		1
91	Efficiency of GaInAs/GaAs quantum-well lasers upon inhomogeneous excitation of quantum wells. <i>Quantum Electronics</i> , 2013 , 43, 999-1002	1.8	5
90	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. <i>Journal of Physics: Conference Series</i> , 2013 , 461, 012038	0.3	1

89	Picosecond photoluminescence dynamics in an InGaAs/GaAs quantum-well heterostructure. <i>Semiconductors</i> , 2012 , 46, 917-920	0.7	4
88	Study of lifetimes and photoconductivity relaxation in heterostructures with Hg _x Cd _{1-x} Te/Cd _y Hg _{1-y} Te quantum wells. <i>Semiconductors</i> , 2012 , 46, 1362-1366	0.7	27
87	Features in the impurity photoconductivity spectra of n-GaAs and n-InP at energies multiple of the optical phonon energy. <i>Semiconductor Science and Technology</i> , 2012 , 27, 115008	1.8	
86	Near-field mechanism of photoluminescence excitation in quantum well heterostructures. <i>JETP Letters</i> , 2012 , 94, 811-815	1.2	1
85	Mode structure in the far field radiation of a leaky-wave multiple quantum well laser. <i>Quantum Electronics</i> , 2012 , 42, 931-933	1.8	9
84	Resonance Coulomb scattering by shallow donor impurities in GaAs and InP. <i>Semiconductor Science and Technology</i> , 2011 , 26, 095003	1.8	1
83	Terahertz surface plasmons in optically pumped graphene structures. <i>Journal of Physics Condensed Matter</i> , 2011 , 23, 145302	1.8	127
82	Cyclotron resonance and interband optical transitions in HgTe/CdTe(0 1 3) quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125011	1.8	37
81	Optical detection of an electric field in a GaAs/AlGaAs n-i-n heterostructure with double quantum wells. <i>JETP Letters</i> , 2011 , 93, 394-398	1.2	
80	Simultaneous TE ₁ and TE ₂ mode lasing yielding dual-wavelength oscillation in a semiconductor laser with a tunnel junction. <i>Semiconductors</i> , 2011 , 45, 641-645	0.7	3
79	Theory of the Fano resonance in impurity excitation spectra of p-GaAs. <i>Physics of the Solid State</i> , 2011 , 53, 1176-1185	0.8	1
78	Polarization dependence of Fano resonances in impurity photoconductivity of quantum wells doped with shallow donors. <i>Physics of the Solid State</i> , 2011 , 53, 1253-1262	0.8	
77	Anomalous characteristics of lasers with a large number of quantum wells. <i>Technical Physics</i> , 2011 , 56, 1049-1052	0.5	3
76	Direct band Ge and Ge/InGaAs quantum wells in GaAs. <i>Journal of Applied Physics</i> , 2011 , 109, 123107	2.5	11
75	Calculation of the parameters for the Fano resonance in the impurity photocurrent spectrum of semiconductors doped with hydrogen-like donors. <i>Semiconductor Science and Technology</i> , 2011 , 26, 049501	1.8	18
74	Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. <i>JETP Letters</i> , 2010 , 92, 756-761	1.2	24
73	Leaky-wave semiconductor laser with improved energetic characteristics and very narrow directional pattern. <i>Quantum Electronics</i> , 2010 , 40, 855-857	1.8	4
72	Calculation of the parameters for the Fano resonance in the impurity photocurrent spectrum of semiconductors doped with hydrogen-like donors. <i>Semiconductor Science and Technology</i> , 2010 , 25, 085005	1.8	2

71	Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. <i>Semiconductors</i> , 2010 , 44, 1394-1397	0.7	9
70	Efficient generation of the first waveguide mode in the InGaAs/GaAs/InGaP heterolaser 2010 , 42, 354		
69	High-field splitting of the cyclotron resonance absorption in strained p-InGaAs/GaAs quantum wells. <i>Physical Review B</i> , 2009 , 79,	3.3	14
68	Intracavity terahertz difference-frequency generation in an InGaAs-quantum-well two-frequency InGaAsP/InP laser. <i>Quantum Electronics</i> , 2009 , 39, 727-730	1.8	4
67	Terahertz laser based on optically pumped graphene: Model and feasibility of realization. <i>JETP Letters</i> , 2009 , 89, 63-67	1.2	31
66	Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. <i>Journal of Experimental and Theoretical Physics</i> , 2009 , 109, 466-471	1	3
65	Difference-frequency generation in a butt-joint diode laser. <i>Semiconductors</i> , 2009 , 43, 208-211	0.7	4
64	Simultaneous generation of TE 0 and TE 1 modes with different wavelengths in a semiconducting laser diode. <i>Technical Physics</i> , 2009 , 54, 1711-1713	0.5	
63	Feasibility of terahertz lasing in optically pumped epitaxial multiple graphene layer structures. <i>Journal of Applied Physics</i> , 2009 , 106, 084507	2.5	109
62	Impurity photoconductivity in strained p-InGaAs/GaAsP heterostructures. <i>JETP Letters</i> , 2008 , 88, 197-200.		
61	Tunable source of terahertz radiation based on the difference-frequency generation in a GaP crystal. <i>JETP Letters</i> , 2008 , 88, 787-789	1.2	8
60	Room-temperature intracavity difference-frequency generation in butt-joint diode lasers. <i>Applied Physics Letters</i> , 2008 , 92, 021122	3.4	17
59	Generation of difference-frequency radiation in the far- and mid-IR ranges in a two-chip laser based on gallium arsenide on a germanium substrate. <i>Quantum Electronics</i> , 2008 , 38, 855-858	1.8	1
58	Generation of difference-frequency radiation in mid- and far-IR ranges by using subpicosecond and picosecond semiconductor lasers. <i>Quantum Electronics</i> , 2008 , 38, 149-153	1.8	2
57	Efficient generation of the first waveguide mode in the InGaAs/GaAs/InGaP heterolaser. <i>Semiconductors</i> , 2008 , 42, 354-357	0.7	0
56	Exchange enhancement of the g factor in InAs/AlSb heterostructures. <i>Semiconductors</i> , 2008 , 42, 828-833.	0.7	31
55	Impurity resonance states in semiconductors. <i>Semiconductors</i> , 2008 , 42, 880-904	0.7	12
54	Fano resonance in the impurity photoconductivity spectrum of InP doped with shallow donors. <i>Physics of the Solid State</i> , 2008 , 50, 1211-1214	0.8	3

53	Experimental study of nonlinear mode mixing in dual-wavelength semiconductor lasers. <i>Laser Physics</i> , 2007 , 17, 684-687	1.2	1
52	Difference-frequency pulse generation in quantum well heterolasers. <i>Laser Physics</i> , 2007 , 17, 688-694	1.2	1
51	Picosecond kinetics of photoexcited carriers in gallium arsenide containing aluminum nanoclusters. <i>Semiconductors</i> , 2007 , 41, 909-913	0.7	2
50	A multifrequency interband two-cascade laser. <i>Semiconductors</i> , 2007 , 41, 1209-1213	0.7	4
49	Frequency shift in a system of two laser diodes. <i>Semiconductors</i> , 2007 , 41, 1364-1368	0.7	1
48	Optical band gap width in GaAs in megagauss magnetic fields. <i>Physics of the Solid State</i> , 2007 , 49, 634-645.8		1
47	Study of interband cascade lasers with tunneling transition. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2007 , 71, 96-99	0.4	
46	Generation of self-sustained pulsations of radiation in InGaAs/GaAs/InGaP quantum-well lasers. <i>Journal of Applied Spectroscopy</i> , 2007 , 74, 589-593	0.7	
45	Monte Carlo simulation of 2D TASER. <i>Journal of Computational Electronics</i> , 2007 , 6, 45-48	1.8	3
44	THE MONTE-CARLO SIMULATION OF TRANSPORT IN QUANTUM WELL GaAs/AlGaAs HETEROSTRUCTURE DOPED WITH SHALLOW DONORS UNDER IMPURITY BREAKDOWN. <i>International Journal of Nanoscience</i> , 2007 , 06, 253-256	0.6	
43	Fano resonance study in impurity photocurrent spectra of bulk GaAs and GaAs quantum wells doped with shallow donors. <i>Physical Review B</i> , 2007 , 75,	3.3	8
42	Nonlinear mode mixing in dual-wavelength semiconductor lasers with tunnel junctions. <i>Applied Physics Letters</i> , 2007 , 90, 171106	3.4	13
41	Parametric optimization of the Bragg reflectors in a laser with the vertical cavity and nonlinear frequency conversion. <i>Semiconductors</i> , 2006 , 40, 486-490	0.7	
40	Oscillations at a difference frequency in the middle and far infrareds in GaP semiconductor waveguides. <i>Technical Physics</i> , 2006 , 51, 1207-1209	0.5	2
39	Spectra of persistent photoconductivity in InAs/AlSb quantum-well heterostructures. <i>Semiconductors</i> , 2005 , 39, 22	0.7	15
38	Calculation of the states of shallow donors in quantum wells in a magnetic field using plane wave expansion. <i>Semiconductors</i> , 2005 , 39, 54	0.7	1
37	Cyclotron resonance in doped and undoped InAs/AlSb heterostructures with quantum wells. <i>Semiconductors</i> , 2005 , 39, 62	0.7	15
36	Terahertz oscillator based on nonlinear frequency conversion in a double vertical cavity. <i>Semiconductors</i> , 2005 , 39, 113	0.7	7

35	Observation of the middle-infrared emission from semiconductor lasers generating two frequency lines in the near-infrared region of the spectrum. <i>Semiconductors</i> , 2005 , 39, 139	0.7	
34	The mode competition, instability, and second harmonic generation in dual-frequency InGaAs/GaAs/InGaP lasers. <i>Semiconductors</i> , 2005 , 39, 156	0.7	5
33	Negative photoconductivity of selectively doped SiGe/Si: B heterostructures with a two-dimensional hole gas in the middle-infrared range. <i>Physics of the Solid State</i> , 2005 , 47, 46	0.8	1
32	Shallow acceptor levels in Ge/GeSi heterostructures with quantum wells in a magnetic field. <i>Physics of the Solid State</i> , 2005 , 47, 76	0.8	
31	Fano resonances in the impurity photoexcitation spectra of semiconductors doped with shallow donors. <i>Journal of Experimental and Theoretical Physics</i> , 2005 , 101, 708-716	1	3
30	Non-linear wave mixing in GaAs/InGaAs/InGaP butt-joint diode lasers. <i>Journal of Modern Optics</i> , 2005 , 52, 2323-2330	1.1	11
29	Shallow-impurity-assisted transitions in the course of submillimeter magnetoabsorption of strained Ge/GeSi(111) quantum-well heterostructures. <i>Physics of the Solid State</i> , 2004 , 46, 125-129	0.8	2
28	Intersubband cyclotron resonance of holes in strained Ge/GeSi(111) heterostructures with germanium wide quantum wells and cyclotron resonance of 1L electrons in GeSi layers. <i>Physics of the Solid State</i> , 2004 , 46, 130-137	0.8	2
27	Blue-green radiation in GaAs-based quantum-well lasers. <i>Semiconductors</i> , 2004 , 38, 352-354	0.7	2
26	Terahertz oscillator with vertical radiation extraction. <i>Technical Physics</i> , 2004 , 49, 592-597	0.5	1
25	Impurity absorption of light involving resonant states of shallow donors in quantum wells. <i>Journal of Experimental and Theoretical Physics</i> , 2004 , 98, 1174-1182	1	0
24	Nonlinear frequency conversion in a double vertical-cavity surface-emitting laser. <i>Semiconductors</i> , 2004 , 38, 1350-1355	0.7	5
23	Nonlinear mid-IR radiation in two-frequency semiconductor lasers with a corrugated waveguide. <i>Technical Physics</i> , 2004 , 49, 1486-1490	0.5	1
22	On the impurity photoconductivity of uniaxially stressed p-Ge. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 680-682		4
21	Population inversion between Γ subbands in quantum wells under the conditions of Γ -intervalley transfer. <i>Semiconductors</i> , 2003 , 37, 215-219	0.7	1
20	Inversion of the electron population in subbands of dimensional quantization with longitudinal transport in tunnel-coupled quantum wells. <i>Semiconductors</i> , 2002 , 36, 685-690	0.7	4
19	Analysis of gain and loss anisotropy in the guiding structure of a long-wave intervalley-transfer laser. <i>Technical Physics</i> , 2002 , 47, 788-791	0.5	
18	Difference mode generation in injection lasers. <i>Semiconductors</i> , 2001 , 35, 1203-1207	0.7	16

17	Resonant states of shallow acceptors in uniaxially deformed germanium. <i>Journal of Experimental and Theoretical Physics</i> , 2001 , 93, 1296-1301	1	5
16	Shallow acceptors in strained Ge/Ge _{1-x} Si _x heterostructures with quantum wells. <i>Semiconductors</i> , 2000 , 34, 563-567	0.7	19
15	Zero-phonon and dipole π electron transitions in GaAs/AlAs quantum-well heterostructures in a longitudinal electric field. <i>Semiconductors</i> , 2000 , 34, 575-582	0.7	
14	The use of a scanning tunneling microscope (STM) for investigation of local photoconductivity of quantum-dimensional semiconductor structures. <i>Technical Physics Letters</i> , 2000 , 26, 1-3	0.7	3
13	Diagnostics of the hot-hole distribution function in quantum wells in a strong electric field. <i>Semiconductors</i> , 2000 , 34, 1073-1078	0.7	
12	Determination of the density of states in quantum wells and quantum dot arrays by the capacitance-voltage method. <i>Semiconductors</i> , 1999 , 33, 1133-1138	0.7	6
11	Characterization of GaAs/In _x Ga _{1-x} As quantum-dot heterostructures by electrical and optical methods. <i>Semiconductors</i> , 1998 , 32, 99-104	0.7	
10	Deep states in silicon δ -doped GaAs. <i>Semiconductors</i> , 1998 , 32, 659-664	0.7	2
9	Polarization of in-plane photoluminescence from InAs/Ga(In)As quantum-well layers grown by metallorganic vapor-phase epitaxy. <i>Semiconductors</i> , 1998 , 32, 1119-1124	0.7	1
8	Shallow acceptors in strained multiquantum-well Ge/Ge _{1-x} Si _x heterostructures. <i>Semiconductors</i> , 1998 , 32, 1106-1110	0.7	1
7	Self-organization of germanium nanoislands obtained in silicon by molecular-beam epitaxy. <i>JETP Letters</i> , 1998 , 67, 48-53	1.2	27
6	Giant population inversion of hot electrons in GaAs/AlAs type heterostructures with quantum wells. <i>JETP Letters</i> , 1998 , 68, 78-83	1.2	7
5	GaAsSb/GaAs quantum well growth by MOCVD hydride epitaxy with laser sputtering of antimony. <i>JETP Letters</i> , 1998 , 68, 91-96	1.2	1
4	Electron and hole spectra and selection rules for optical transitions in Ge _{1-x} Si _x /Ge heterostructures. <i>Semiconductors</i> , 1997 , 31, 132-138	0.7	7
3	Photoelectric properties of GaAs/InAs heterostructures with quantum dots. <i>Semiconductors</i> , 1997 , 31, 941-946	0.7	7
2	Far Infrared Emission and Absorption (Amplification) under Real Space Transfer and Population Inversion in Shallow Multi-Quantum-Wells. <i>Physica Status Solidi (B): Basic Research</i> , 1997 , 204, 563-565	1.3	3
1	Infrared radiation from hot holes during spatial transport in selectively doped InGaAs/GaAs heterostructures with quantum wells. <i>JETP Letters</i> , 1996 , 64, 520-524	1.2	5